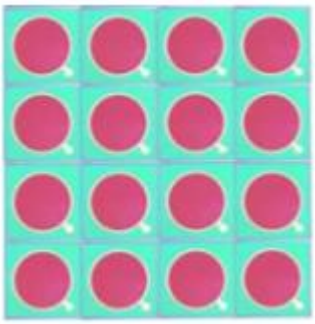
1260-1620nm InGaAs PIN Photodiode Chip, Dia. 1.0mm Active Area

Part No. PDC-13A1000

Features



- 1310nm/1550nm InGaAs PIN photodiode chip
- Dia. 1.0mm Active window
- Optical power monitor PD
- Low dark current and low capacitance

Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage temperature	-40	100	ºC	
Operating temperature	-40	85	ºC	
Forward current		10	mA	
Reverse current		2	mA	
Reverse voltage		20	V	

Electro-Optical Characteristics						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Responsivity	R	0.8	0.95		A/W	V_R = 5V, λ = 1310nm@25ºC
Dark current	I_D		2	20	nA	V_R = 5V@25ºC
Breakdown voltage	V_{BD}	20	35		V	I_R = 10μA
Capacitance	C		100	200	pF	V_R = 0V, f = 1MHz

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Typical Characteristics

Fig. 1 Typical Dark Current vs. Forward Current

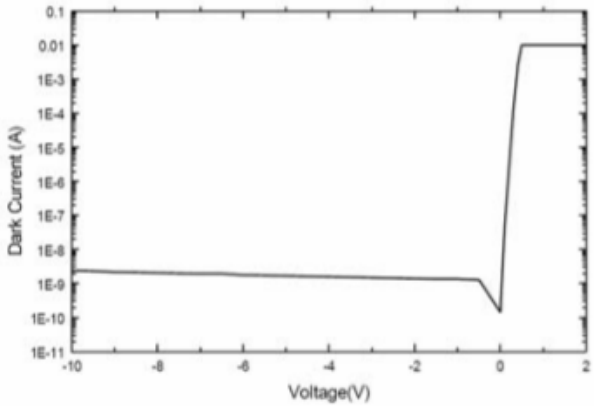


Fig. 2 Typical Photo-Current

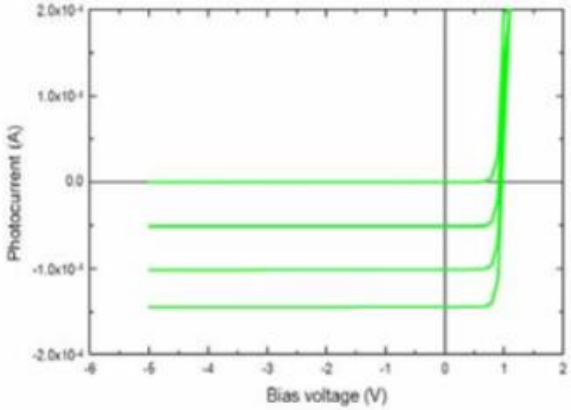


Fig. 3 Typical Breakdown Curve

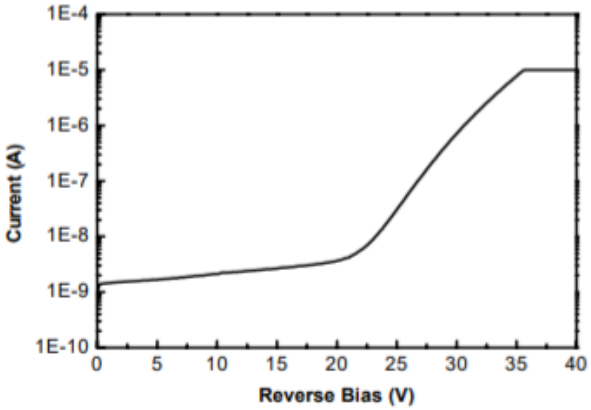
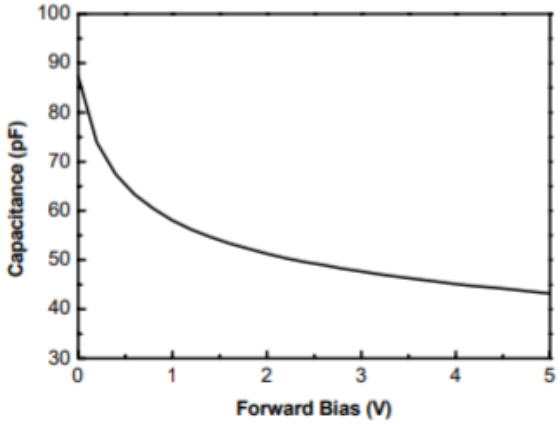
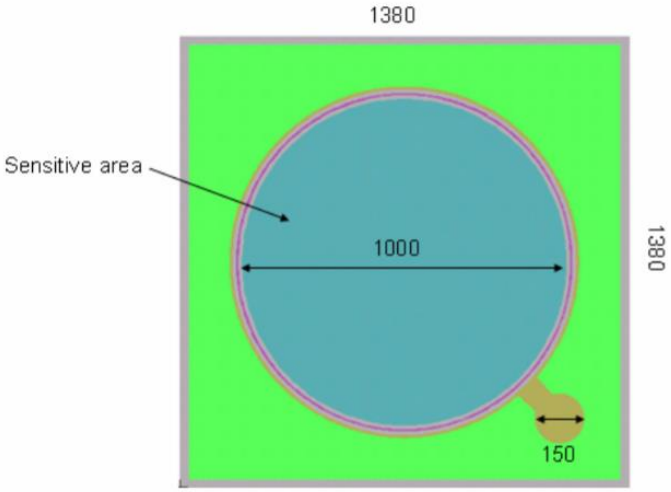


Fig. 4 Typical C-V Curve



Outline Diagram



- Chip size: 1380μm x 1380μm typical
- Chip thickness: 200μm ±30μm
- Sensitive area: Typical 1000μm in diameter

Note: Specifications are subject to change without notice.

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